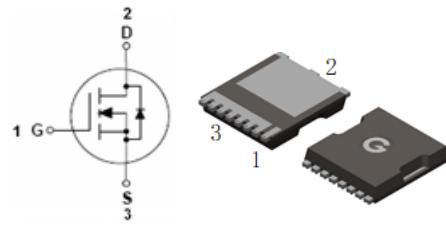


Features

- Ultra-low on-resistance and gate-charge
- Advanced shielded-gate technology
- JESD22-A114-B ESD rating of class 3A per human body model

HF

TOLL

Mechanical Data

- Case: TOLL
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL011N06TH-TL	TOLL	2000 pcs / Tape & Reel	011N06TH

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	V
Gate-to-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$, Silicon Limited)	I_D	375	A
Continuous Drain Current ($T_c = 25^\circ\text{C}$, Package Limited)		300	A
Continuous Drain Current ($T_A = 25^\circ\text{C}$)		48	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_c = 25^\circ\text{C}$)	I_{DM}	1200	A
Single Pulse Avalanche Energy ³	E_{AS}	700	mJ
Power Dissipation ($T_c = 25^\circ\text{C}$, $R_{\theta JC} = 0.4^\circ\text{C}/\text{W}$)	P_D	375	W
Operating Junction Temperature Range	T_J	-55 ~ +175	°C
Storage Temperature Range	T_{STG}	-55 ~ +175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	0.4	0.5	°C/W
Thermal Resistance Junction-to-Air ¹	$R_{\theta JA}$	-	22	30	°C/W

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1\text{mA}$	60	-	-	V
$I_{DS(0)}$	Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance ^{*2}	$V_{GS} = 10V, I_D = 80\text{A}$	-	0.78	1.1	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2	3	4	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1\text{MHz}$	-	2.2	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 30V$ $f = 1\text{MHz}$	-	15758	-	pF
C_{OSS}	Output Capacitance		-	5461	-	
C_{RSS}	Reverse Transfer Capacitance		-	177	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time ^{*4}	$V_{DD} = 30V$ $V_{GS} = 10V$ $R_G = 1.8\Omega$ $I_D = 100\text{A}$	-	16	-	ns
t_r	Turn-on Rise Time ^{*4}		-	27	-	
$t_{d(OFF)}$	Turn-Off Delay Time ^{*4}		-	48	-	
t_f	Turn-Off Fall Time ^{*4}		-	23	-	
Q_G	Total Gate-Charge	$V_{DD} = 48V$ $V_{GS} = 10V$ $I_D = 80\text{A}$	-	230	-	nC
Q_{GS}	Gate to Source Charge		-	70	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	50	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*2}	$I_S = 80\text{A}, V_{GS} = 0V$	-	0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_S = 40\text{A}, V_{GS} = 0V$ $di/dt = 100\text{A}/\mu\text{s}$	-	118	-	ns
Q_{rr}	Reverse Recovery Charge		-	350	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 40V, V_{GS} = 10V, L = 1\text{mH}$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

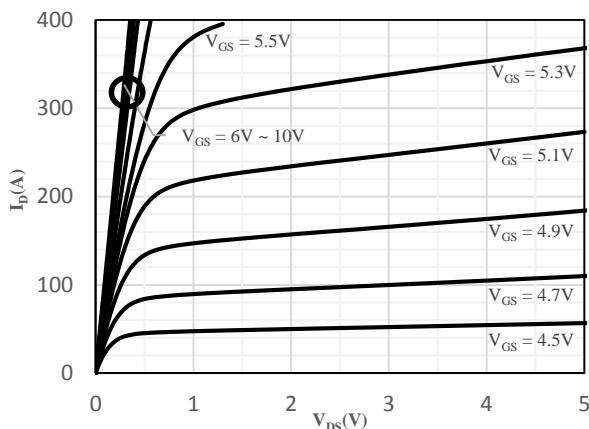


Fig 1 Typical Output Characteristics

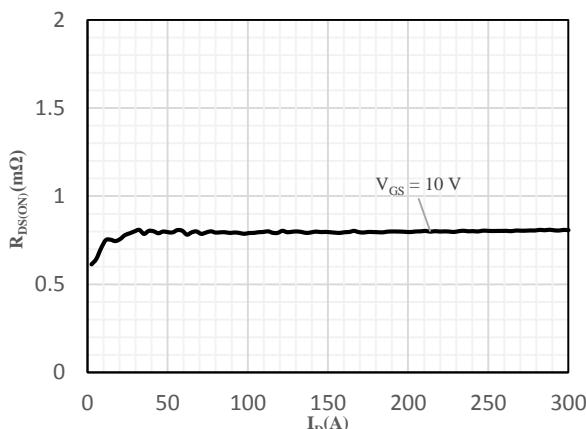


Fig 2 On-Resistance vs. Drain Current and Gate Voltage

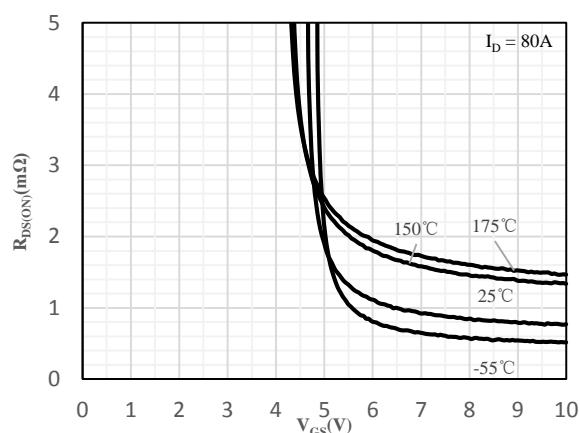


Fig 3 On-Resistance vs. Gate-Source Voltage

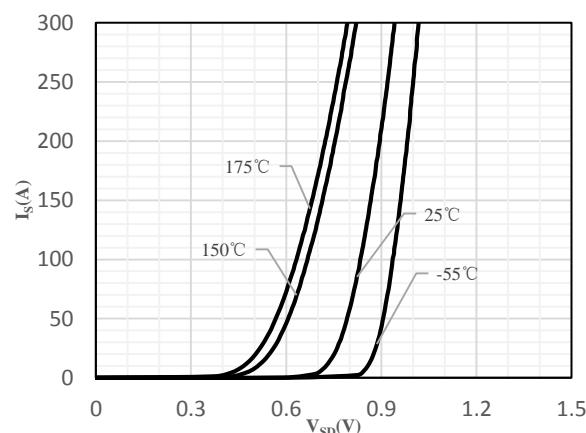


Fig 4 Body-Diode Characteristics

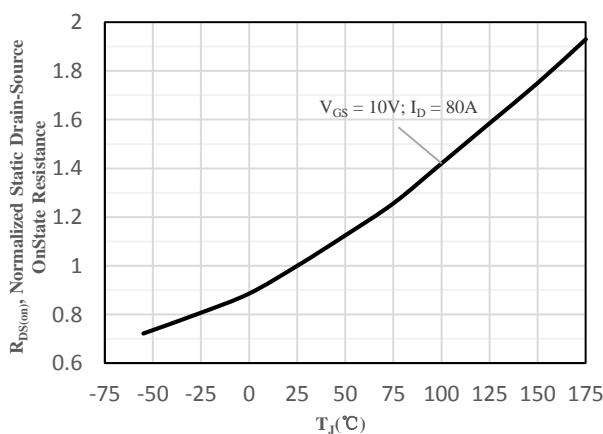


Fig 5 Normalized On-Resistance vs. Junction Temperature

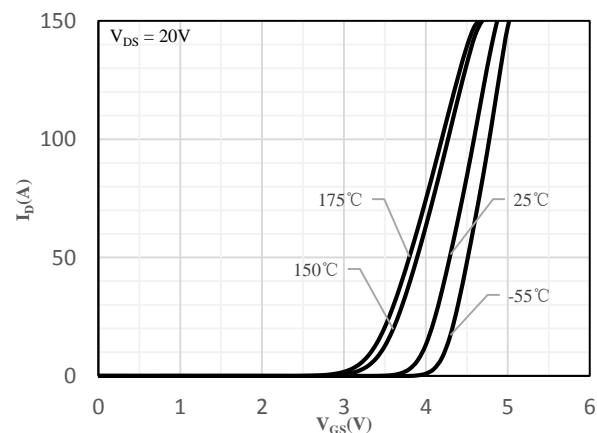


Fig 6 Transfer Characteristics

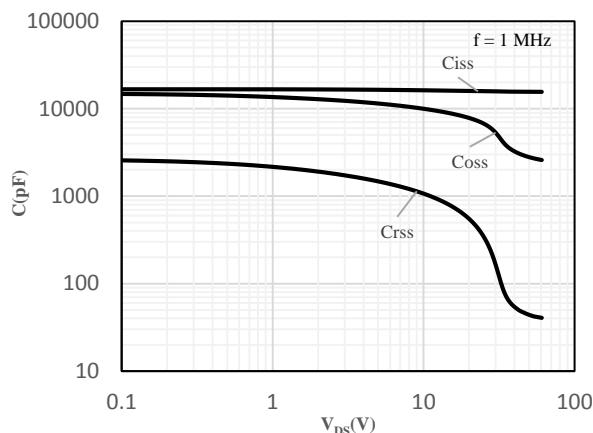


Fig 7 Capacitance Characteristics

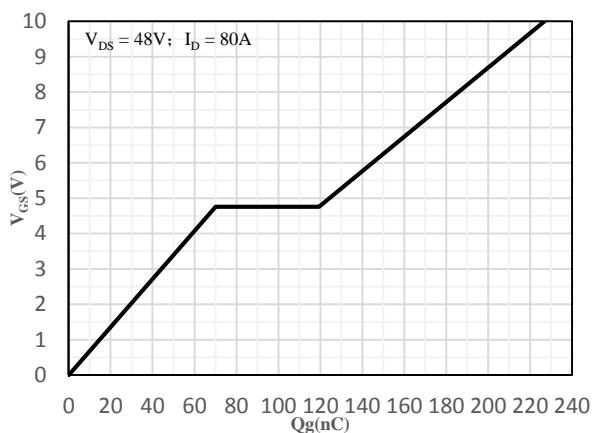


Fig 8 Gate-Charge Characteristics

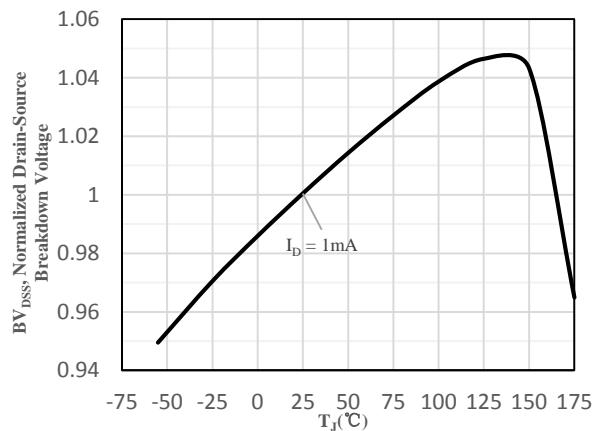


Fig 9 Normalized Breakdown Voltage
vs. Junction Temperature

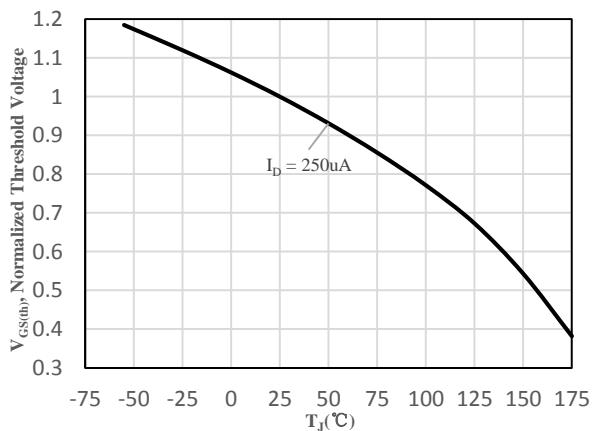


Fig 10 Normalized $V_{GS(th)}$ vs. Junction Temperature

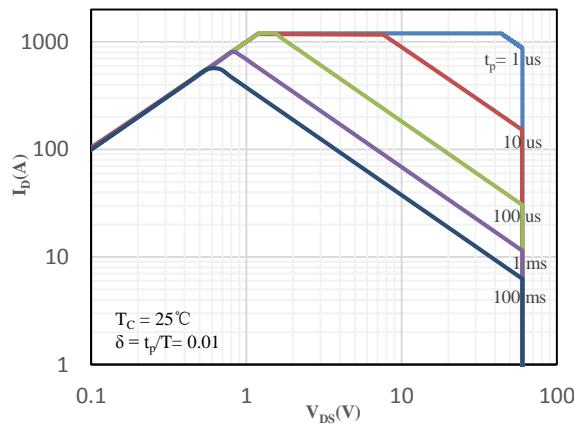


Fig 11 Safe Operation Area

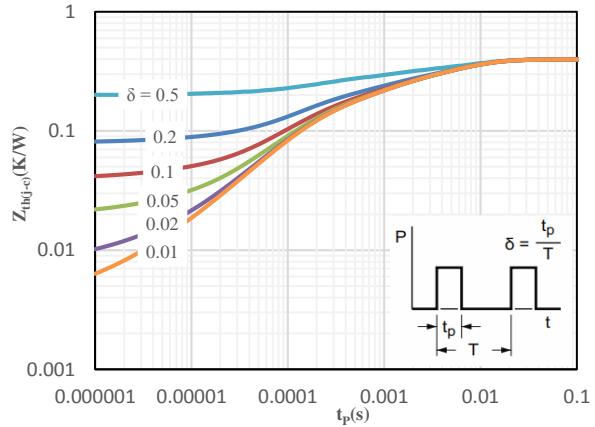
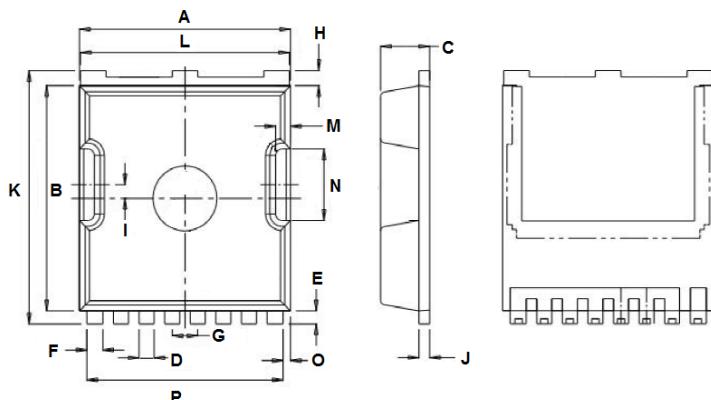


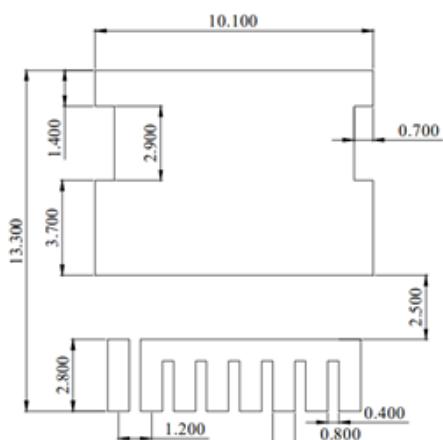
Fig 12 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



TOLL		
Dimension	Min.	Max.
A	9.70	10.10
B	10.20	10.60
C	2.10	2.50
D	0.60	0.80
E	0.50	0.70
F	0.65	0.85
G	1.10	1.30
H	0.60	0.80
I	0.55	0.75
J	0.45	0.55
K	11.50	11.90
L	9.60	10.00
M	0.50	0.70
N	3.10	3.50
O	0.25	0.45
P	9.00	9.40

SOLDERING FOOTPRINT (Unit: mm)



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